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Other Documents (Including Author, Title, Date Pertinent Pages, Etc.) Japanese Office Action dated June 23, 2009 Norio Onojima et al., "Lattice Relaxation Process of AIN Growth on Atomically Flat 6H-SiC Substrate Molecular Beam Epitaxy", Journal of Crystal Growth (2002), pp. 1012-1016	6	Form PTO 1449 U.S. D	ATTY. DOCKET NUMBER HIRA.0204 SERIAL NUMBER 10/549,683 APPLICANT								
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Norio Onojima et al., "Lattice Relaxation Process of AIN Growth on Atomically Flat 6H-SiC Substrate Molecular Beam Epitaxy", Journal of Crystal Growth (2002), pp. 1012-1016 Steve Wright et al., "Reduction of Oxides on Silicon by Heating in a Gallium Molecular Beam at 800°C		Initial					<u> </u>	CLASS	YES	No	
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Norio Onojima et al., "Lattice Relaxation Process of AIN Growth on Atomically Flat 6H-SiC Substrate Molecular Beam Epitaxy", Journal of Crystal Growth (2002), pp. 1012-1016 Steve Wright et al., "Reduction of Oxides on Silicon by Heating in a Gallium Molecular Beam at 800°C	}			 		ļ		 		┼─	
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				Steve Wright et al., "Reduction of Oxides on Silicon by Heating in a Gallium Molecular Beam at 800°C*". Appl. Phys. Lett, Vol. 36, No. 3, 1 February 1980, pp. 210-211							
		 									
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